

| L Number | Hits | Search Text  | DB  | Time stamp       |
|----------|------|--|---|------------------|
| 1        | 3702 | ((257/296) or (257/401) or (257/410)).CCLS.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/06 16:38 |
| 2        | 0    | ((257/296) or (257/401) or (257/410)).CCLS.) and "bird's beak" near4 gate near4 underneath and silicon adj nitride   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/06 16:39 |
| -        | 5    | 272,968.ap.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/06 16:38 |
| -        | 1    | "5612249".PN.  | USPAT   | 2002/05/22 14:58 |
| -        | 1    | "5637514".PN.  | USPAT   | 2002/05/22 14:59 |
| -        | 1    | "5798550".PN.  | USPAT   | 2002/05/22 14:59 |
| -        | 1    | "6015736".PN.  | USPAT   | 2002/05/22 15:00 |
| -        | 3    | ("5306655").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 15:43 |
| -        | 3    | ("5360758").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:03 |
| -        | 301  | ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 09:41 |
| -        | 3    | ("5382533").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:51 |
| -        | 3    | ("5679968").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:52 |
| -        | 3    | ("5714413").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:53 |
| -        | 0    | ("ep-621632\$-\$\$.did.").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:53 |
| -        | 0    | ("ep-621632\$-\$\$.did.").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:53 |
| -        | 0    | rajeevakumar.in. and dram adj cell adj structure   | EPO   | 2002/05/22 17:55 |
| -        | 6    | rajeevakumar.in. and dram adj cell adj structure   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22 17:55 |

|   |        |   |   |                  |
|---|--------|---|---|------------------|
| - | 3      | ("5612249").PN.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:42 |
| - | 0      | earom and selection same transistor same dram   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:43 |
| - | 27     | earom and transistor same dram  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:44 |
| - | 6      | earom and transistor same dram.ti,ab.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:45 |
| - | 109394 | earom.ti,ab. and dram.ti,ab. and 257/\$6.ccls. or 438/\$6.ccls.                                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:46 |
| - | 5      | earom.ti,ab. and dram.ti,ab.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:47 |
| - | 187    | selection near12 (transistor or fet or mosfet) near12 dram                                      | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 10:49 |
| - | 44     | (selection near6 (transistor or fet or mosfet) near6 dram) and (257/\$6.ccls. or 438/\$6.ccls.) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 12:09 |
| - | 3      | ("5854500").PN.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 12:14 |
| - | 2      | ("6037639").PN.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 13:57 |
| - | 1962   | (257/296).CCLS.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 12:26 |
| - | 1041   | (257/401).CCLS.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 15:08 |
| - | 432    | (257/410).CCLS.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/23 15:08 |
| - | 2      | ("5885553").PN.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/06 10:35 |

|   |     |   |   |                  |
|---|-----|---|---|------------------|
| - | 2   | ("5612249").PN.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/11/06 12:04 |
| - | 0   | (side adj wall or sidewall) near12 gate<br>adj oxide near12 silicon adj nitride adj<br>spacer           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/11/06 12:06 |
| - | 15  | (side adj wall or sidewall) near12 gate<br>adj oxide near12 silicon adj nitride                         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/11/06 12:07 |
| - | 147 | oxidation adj barrier near4 oxide   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/11/06 13:06 |
| - | 201 | (MOS or MOSFET).ti,ab,clm. and silicon adj<br>nitride near4 (sidewall or side adj wall)<br>near4 spacer | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/11/06 13:09 |